



Product Overview

NTS2101P: Small Signal MOSFET -8V -1.4A 100 mOhm Single P-Channel SC-70

For complete documentation, see the data sheet

Product Description

This is an 8.0 V P-Channel Power MOSFET.

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Extending Battery Life
- -1.8 V Rated for Low Voltage Gate Drive
- SC-70 Surface Mount for Small Footprint (2x2 mm)
- Pb-Free Package is Available

Applications

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Application Applications such as Cell Phones, Digital Cameras, PDAs, etc.

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(sat)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTS2101PT1G	Pb-free Halide free	Active	P-Channel	Single	8	8	0.7	1.4	0.29	140	100	210	6.4		1.5	9.5	640	120	82	SC-70-3 / SOT-323-3

For more information please contact your local sales support at www.onsemi.com

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